



**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

1.-10. (Canceled)

1 11 (Previously Presented) A silicon carbide component for a semiconductor substrate processing apparatus, the silicon carbide component being porous and comprising an interior and an exposed surface, the silicon carbide component having been (i) made by a graphite conversion process that results in the silicon carbide component including free-carbon in graphite form in the interior; (ii) treated to produce an exposed surface having the free-carbon in graphite form therein; and (iii) treated to remove the free-carbon such that at least the exposed surface is substantially free of the free-carbon, wherein the silicon carbide component is selected from the group consisting of a baffle plate, a plasma confinement ring and an edge ring.

2 12 (Previously Presented) The silicon carbide component of Claim 11, wherein the silicon carbide component is a baffle plate.

3 13 (Original) A semiconductor substrate processing apparatus comprising a plasma processing chamber and at least one silicon carbide component according to Claim 11 in the plasma processing chamber.

4 14. (Original) The semiconductor substrate processing apparatus of Claim 13, wherein the plasma processing chamber is an etching chamber.

15.-28. (Canceled)

5 29. (Previously Presented) The silicon carbide component of Claim 11, wherein the silicon carbide component has been treated and has not been installed in the semiconductor substrate processing apparatus.

6 30. (Previously Presented) The silicon carbide component of Claim 11, wherein the silicon carbide component has been treated in an oxygen-containing atmosphere in a treatment vessel and has not been installed in the semiconductor substrate processing apparatus.

7 31. (Previously Presented) A semiconductor substrate processing apparatus comprising the silicon carbide component according to Claim 11.

8 32. (Previously Presented) The silicon carbide component of Claim 11, wherein the graphite comprises graphite clusters having a size of about 20  $\mu\text{m}$  to about 200  $\mu\text{m}$ .

9 33. (Previously Presented) The silicon carbide component of Claim 11, wherein the exposed surface is a machined surface substantially free of the free-

carbon and the interior of the silicon carbide component contains free-carbon in graphite form.

10 34. (Previously Presented) The silicon carbide component of Claim 11, wherein the silicon carbide component has a thickness of up to about  $\frac{1}{4}$  inch.

12 35. (Previously Presented) A silicon carbide component for a semiconductor substrate processing apparatus, the silicon carbide component comprising an interior and an exposed surface, the interior containing free-carbon in graphite form and the exposed surface being substantially free of the free-carbon, wherein the silicon carbide component is selected from the group consisting of a baffle plate, a plasma confinement ring and an edge ring.

13 36. (Previously Presented) The silicon carbide component of Claim 35, wherein the silicon carbide component is a baffle plate

14 37. (Previously Presented) The silicon carbide component of Claim 35, wherein the silicon carbide component has been treated and has not been installed in the semiconductor substrate processing apparatus.

15 38. (Previously Presented) The silicon carbide component of Claim 35, wherein the silicon carbide component has been treated in an oxygen-containing atmosphere in a treatment vessel and has not been installed in the semiconductor substrate processing apparatus.

16 39. (Previously Presented) A semiconductor substrate processing apparatus comprising the silicon carbide component according to Claim 35.

17 40. (Previously Presented) The silicon carbide component of Claim 35, wherein the graphite comprises graphite clusters having a size of about 20  $\mu\text{m}$  to about 200  $\mu\text{m}$ .

18 41. (Previously Presented) The silicon carbide component of Claim 35, wherein the exposed surface is a machined surface substantially free of the free-carbon and the interior of the silicon carbide component contains the free-carbon.

19 42. (Previously Presented) The silicon carbide component of Claim 35, wherein the silicon carbide component has a thickness of up to about  $\frac{1}{4}$  inch.

21 43. (Previously Presented) A silicon carbide baffle plate for a semiconductor substrate processing apparatus, the baffle plate comprising an interior and a machined exposed surface, the interior containing free-carbon particles or clusters in graphite form and the exposed surface being substantially free of the free-carbon.

22 44. (Previously Presented) The silicon carbide baffle plate of Claim 43, wherein the silicon carbide component has been treated and has not been installed in the semiconductor substrate processing apparatus.

11 45. (New) The silicon carbide component of Claim 11, wherein (iii) comprises heating the silicon carbide component including free-carbon in an oxygen-containing atmosphere to remove all of the free-carbon at the exposed surface and at least about 80% of the number of particles and/or clusters of the graphite sized above about 50  $\mu\text{m}$  in the interior.

20 46. (New) The silicon carbide component of Claim 35, wherein the silicon carbide component including free-carbon has been treated in an oxygen-containing atmosphere to remove all of the free-carbon at the exposed surface and at least about 80% of the number of particles and/or clusters of the graphite sized above about 50  $\mu\text{m}$  in the interior.

23 47. (New) The silicon carbide component of Claim 43, wherein the silicon carbide baffle plate including free-carbon has been treated in an oxygen-containing atmosphere to remove all of the free-carbon at the exposed surface and at least about 80% of the number of the particles and/or clusters above about 50  $\mu\text{m}$  in the interior.